

MOS INTEGRATED CIRCUIT μ PD17P133

SMALL GENERAL-PURPOSE 4 BIT SINGLE-CHIP MICROCONTROLLER

The μ PD17P133 is a one-time PROM version of the μ PD17133, in which the internal masked ROM of the μ PD17133 is replaced with a one-time PROM that can be written to just once.

Since user programs can be written to the PROM, this microcontroller is suited for program evaluation and small-lot production of the μ PD17121/ μ PD17133, or for program evaluation of the μ PD17133(A).

The following user's manual completely describes the functions of the μ PD17P133. Be sure to read it before designing an application system.

μPD17120 Sub-Series User's Manual: IEU-1367

FEATURES

- 17K architecture : General registers
- Upward compatible with the μ PD17121
- Pin compatible with the μ PD17133 (except for PROM programming function)
- Internal one-time PROM: 2K bytes (1024 \times 16 bits)
- Supply voltage
 : VDD = 2.7 to 5.5 V (fx = 400 kHz to 4 MHz)
 VDD = 4.5 to 5.5 V (fx = 400 kHz to 8 MHz)

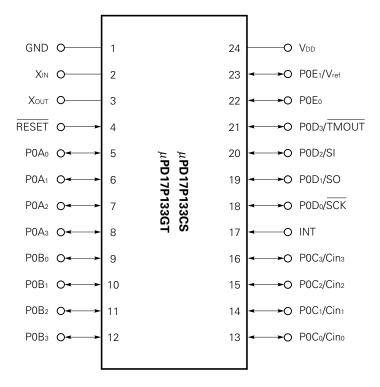
ORDERING INFORMATION

Part number	Package
μPD17P133CS	24-pin plastic shrink DIP (300 mil)
μPD17P133GT	24-pin plastic SOP(375 mil)

The information in this document is subject to change without notice.

PIN CONFIGURATION (TOP VIEW)

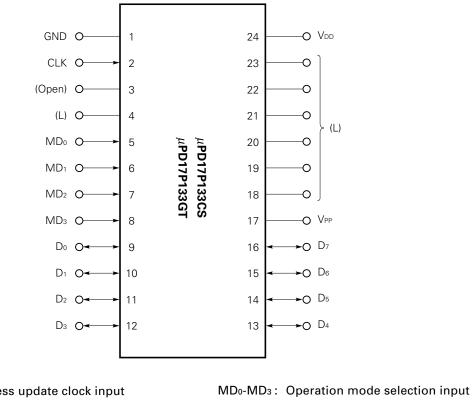
(1) Normal operating mode



Cino-Cin ₃ :	Comparator input
GND :	Ground
INT :	External interrupt input
P0A0-P0A3:	Port 0A
P0B0-P0B3:	Port 0B
P0C0-P0C3:	Port 0C
P0D0-P0D3:	Port 0D

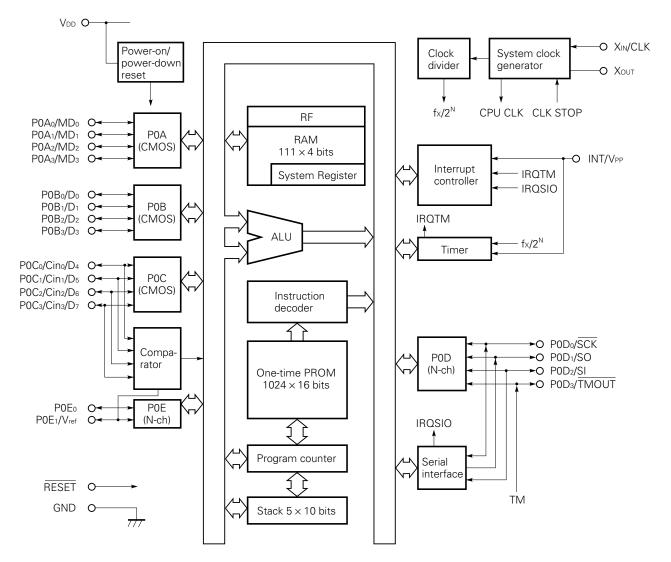
P0E0, P0E1	:	Port 0E
RESET	:	Reset input
SCK	:	Serial clock input/output
SI	:	Serial data input
SO	:	Serial data output
TMOUT	:	Timer output
Vdd	:	Positive power supply
Vref	:	External reference voltage input
XIN, XOUT	:	System clock oscillation

(2) Program memory write/verify mode



- CLK : Address update clock inputMD0-MD3: Operation mode selection inpuD0-D7: Data input/outputVDD : Power supplyGND: GroundVPP : Programming power supply
 - Caution Symbols in parentheses denote processing for pins not used in the program memory write/verify mode.
 - L: Connect these pins separately to the GND pin through pull-down resistors.
 - Open: Nothing should be connected on these pins.

BLOCK DIAGRAM



RemarkThe terms CMOS and N-ch in parentheses indicate the output form of the port.

CMOS: CMOS push-pull output

N-ch: N-channel open-drain output

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1. PIN FUNCTIONS

1.1 NORMAL OPERATION MODE

Pin No.	Pin name	Function	Output	At reset
1	GND	Ground	_	_
2 3	Xin Xout	For system clock oscillation. Ceramic resonator is connected with these pins.	_	_
4	RESET	System reset input pin	_	Input
5 to 8	P0A₀ to P0A₃	 Port 0A 4-bit input/output port Input/output setting allowed in units of 1 bit 	CMOS push-pull	Input
9 to 12	P0B₀ to P0B₃	Port 0B 4-bit input/output port Input/output setting allowed in units of 4 bits 	CMOS push-pull	Input
13 to 16	P0Co/Cino to P0C₃/Cin₃	 Port 0C. Analog voltage is supplied to the comparator through these pins. POC₀ - POC₃ 4-bit input/output port Input/output setting allowed in units of 1 bit Cin₀ - Cin₃ Analog input for the comparator 	CMOS push-pull	Input (P0C)
17	INT	External interrupt request or sensor signal	-	Input
18 19 20 21	P0D0/SCK P0D1/SO P0D2/SI P0D3/TMOUT	 Pin for port 0D, timer carry output, serial data input, serial data output, and serial clock input/output P0D₀ - P0D₃ 4-bit input/output port Input/output setting allowed in units of 1 bit SCK Serial clock input/output SO Serial data output SI Serial data input TMOUT Timer output 	N-ch open drain	Input (P0D)
22 23	P0Eo P0E1/Vref	 Port 0E. Reference voltage is supplied to the comparator through these pins. Withstand voltage of P0E1 is VpD (MAX.). P0E0 and P0E1 2-bit input/output port Input/output setting allowed in units of 1 bit Vref Input of external reference voltage for the comparator 	N-ch open drain	Input (P0E)
24	Vdd	Power supply pin	_	_

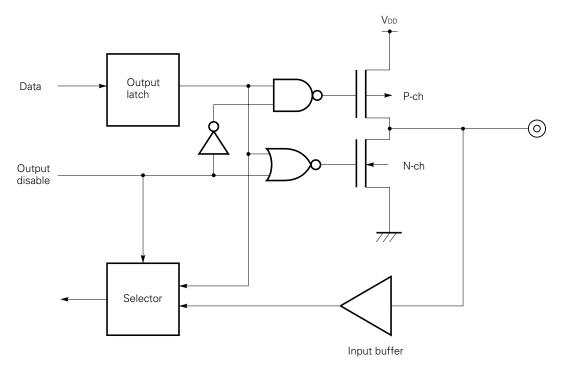
1.2 PROGRAM MEMORY WRITE/VERIFY MODE

Pin No.	Pin name	Function	Input/output
1	GND	Ground	_
2	CLK	Input pin for address update clocks used when writing to program memory or verifying its contents	Input
5	MD ₀	Input pins that select an operation mode when writing to program	Input
to	to	memory or verifying its contents	
8	MD₃		
9	Do	Input/output pins for 8-bit data used when writing to program	Input/output
to	to	memory or verifying its contents	
16	D7		
17	Vpp	Voltage (+12.5 V) is applied to this pin when writing to program memory or verifying its contents.	-
24	Vdd	Power supply pin. +6 V is applied to this pin when writing to program memory or verifying its contents.	-

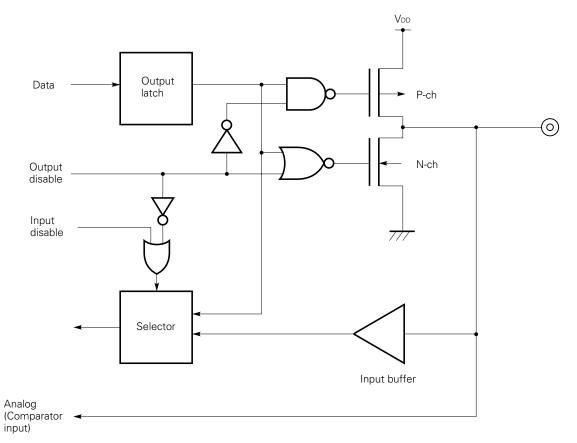
1.3 PIN EQUIVALENT CIRCUIT

Below are simplified diagrams of the input/output circuits for each pin.

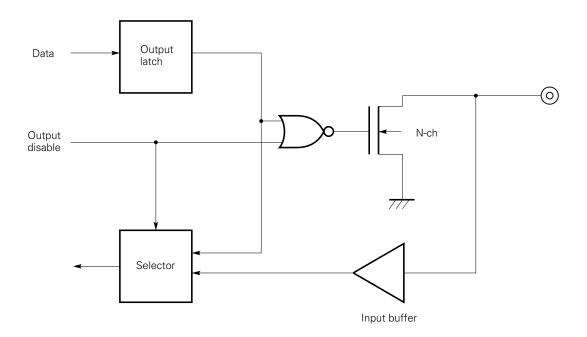
(1) P0A₀ to P0A₃, P0B₀ to P0B₃



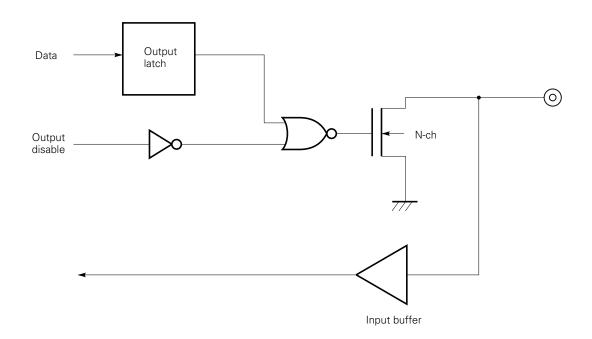
(2) POC 0/Cino to POC 3/Cins



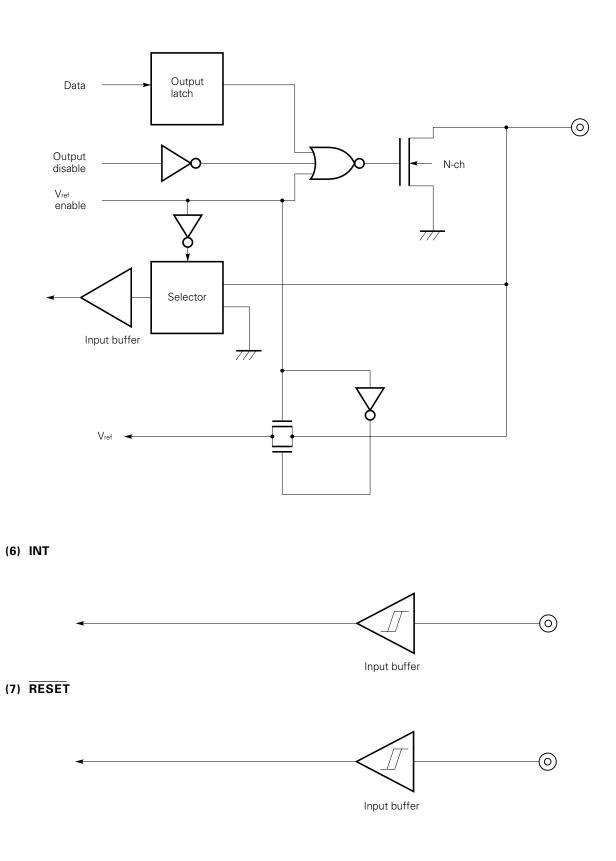
(3) POD₀ to POD₃



(4) POE 0



(5) POE 1/Vef



★ 1.4 HANDLING UNUSED PINS

In normal operation mode, connect unused pins as follows:

Pin		Dia	Recommended conditions and handling		
		FIN	Internal	External	
Port	Input mode	P0A, P0B, P0C, P0D, P0E	_	Connect to VDD or ground through resistors for each pin.Note 1	
Output P0A, P0B, P0C mode (CMOS ports)			_	Leave open.	
		P0D, P0E (N-ch open- drain port)	Outputs low level to pins.		
External interrupt (INT)Note 2		rrupt (INT)Note 2		Connect directly to ground.	
RESETNote 3 (when only the built-in power-on/ power-down reset function is used)		•	_	Connect directly to VDD.	

- **Notes 1.** When a pin is pulled up to VDD (connected to VDD through a resistor) or pulled down to ground (connected to ground through a resistor) outside the chip, take the driving capacity and maximum current consumption of a port into consideration. When using high-resistance pull-up or pull-down resistors, apply appropriate countermeasures to ensure that noise is not attracted by the resistors. Although the optimum pull-up or pull-down resistor varies with the application circuit, in general, a resistor of 10 to 100 kilohms is suitable.
 - **2**. Since the INT pin is also used for setting the test mode, connect it directly to ground when the pin is not used.
 - **3.** When designing an application circuit which requires high reliability, be sure to design a circuit to which an external **RESET** signal can be input. Since the **RESET** pin is also used for setting the test mode, connect it to VDD directly when not used.
- Caution To fix the I/O mode and output level of a pin, it is recommended that they should be specified repeatedly within a loop in a program.

1.5 NOTES ON USE OF THE RESET AND INT PINS (FOR NORMAL OPERATION MODE ONLY)

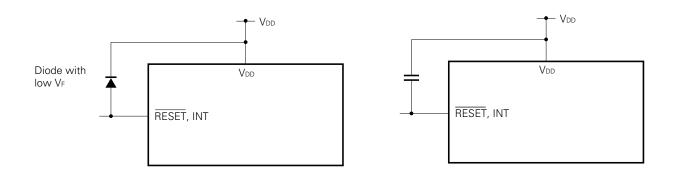
The $\overline{\text{RESET}}$ and INT pins have the test mode selecting function for testing the internal operation of the μ PD17P133 (IC test), besides the functions shown in **Section 1.1**.

Applying a voltage exceeding V DD to the RESET and/or INT pin causes the μ PD17P133 to enter the test mode. When noise exceeding VDD comes in during normal operation, the device is switched to the test mode.

For example, if the wiring from the RESET or INT pin is too long, noise may be induced on the wiring, causing this mode switching.

When installing the wiring, lay the wiring in such a way that noise is suppressed as much as possible. If noise yet arises, use an external part to suppress it as shown below.

Connect a diode with low FVbetween the pin Connect a capacitor between the pin and DV. and Vol.



2. DIFFERENCES BETWEEN THE μ PD17P133, μ PD17121, AND μ PD17133

The μ PD17P133 is a one-time PROM version of the μ PD17133, in which the internal masked ROM is replaced with a one-time PROM.

Table 2-1 lists the differences between the μ PD17P133, μ PD17121, and μ PD17133.

The μ PD17P133 has the same CPU functions and internal peripheral hardwares as those of μ PD17121 and μ PD17133 except for its program memory, program memory size, data memory size, operating frequency range, electrical characteristics, and mask option. The μ PD17P133 can be used for evaluation of programs during μ PD17121/ μ PD17133 system development.

ltem	μPD17P133	μPD17121	μPD17133
Program memory (ROM)	One-time PROM	Masked ROM	
	2K bytes (1024 × 16 bits) (0000H - 03FFH)	1.5K bytes (768 × 16 bits) (0000H - 02FFH)	2K bytes (1024 × 16 bits) (0000H - 03FFH)
Data memory (RAM)	111×4 bits	64×4 bits	111×4 bits
Pull-up resistors of P0D, P0E, and RESET pins	Not provided	Mask option	
V _{PP} and operation mode selection pins	Provided	Not provided	
Comparator	Provided	Not provided	Provided
Withstand voltage of the P0E1 pin ^{Note}	Vdd	9 V	Vdd
Quality grade	Standard		 Standard (μPD17133) Special (μPD17133(A))

Table 2-1 Differences between the µPD17P133, µPD17121, and µPD17133

- **Note** The P0E₁ pin of the μ PD17133 or μ PD17P133 is an N-ch open-drain I/O pin. However, the pin cannot be used as an intermediate-withstand-voltage port pin because this pin is also used as the V ref pin.
- Caution Although a PROM product is highly compatible with a masked ROM product in respect of functions, they differ in internal ROM circuits and part of electrical characteristics. Before changing the PROM product to the masked ROM product in an application system, evaluate the system carefully using the masked ROM product.

3. WRITING TO AND VERIFYING ONE-TIME PROM (PROGRAM MEMORY)

The μ PD17P133's internal program memory consists of a 1024 \times 16 bit one-time PROM.

Writing to the one-time PROM or verifying the contents of the PROM is accomplished using the pins shown in the table below. Note that address inputs are not used; instead, the address is updated using the clock input from the CLK pin.

Table 3-1	Pins Used When	Writing to Program	Memory or	Verifying Its Contents
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Pin name	Function
Vpp	Voltage (+12.5 V) is applied to this pin when writing to program memory or verifying its contents.
Vdd	Power supply pin. +6 V is applied to this pin when writing to program memory or verifying its contents.
CLK	Input pin for address update clocks used when writing to program memory or verifying its contents. Input of four pulses to this pin updates the address of the program memory.
MDo - MD3	Input pins that select an operation mode when writing to program memory or verifying its contents
D0 - D7	Input/output pins for 8-bit data used when writing to program memory or verifying its contents

3.1 PROGRAM MEMORY WRITE/VERIFY MODES

If +6 V is applied to the V DD pin and +12.5 V is applied to the V PP pin after a certain duration of reset status $(V_{DD} = 5 V, \overline{RESET} = 0 V)$, the μ PD17P133 enters program memory write/verify mode. A specific operating mode is then selected by setting the MD $_0$ through MD₃ pins as follows. Connect each pin not listed in Table 3-1 to ground through a pull-down resistor. (However, the X out pin must be left open.)

For details, see PIN CONFIGURATION (2).

Operating mode specification			tion	Operating mode			
Vpp	Vdd	MD₀	MD1	MD ₂	MD₃		
+12.5 V +6 V		н	L	н	L	Program memory address clear mode	
	16 V	L	н	н	н	Write mode	
	+0 0	L	L	н	н	Verify mode	
		н	×	н	Н	Program inhibit mode	

Table 3-2 Specification of Operating Modes

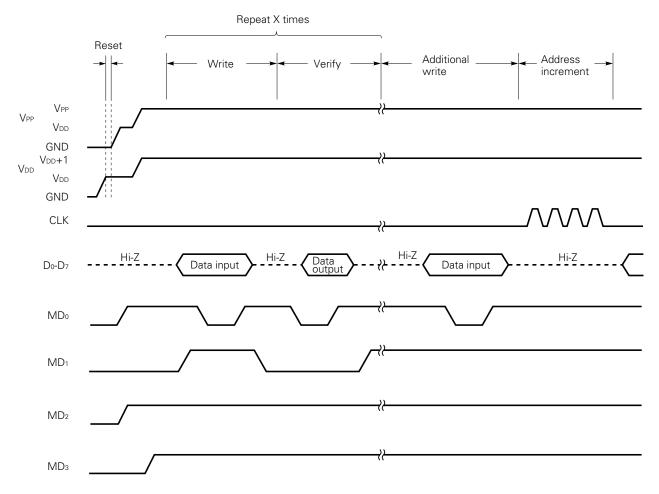
Remark x: Don't care. L (low) or H (high)

3.2 WRITING TO PROGRAM MEMORY

The procedure for writing to program memory is described below; high-speed write is possible.

- (1) Pull low the levels of all unused pins to GND by means of resistors (the X out pin is left open). Bring CLK to low level.
- (2) Apply 5 V to V DD and bring VPP to low level.
- (3) Wait 10 μ s. Then apply 5 V to V PP.
- (4) Set the mode selection pins to program memory address clear mode.
- (5) Apply 6 V to V $_{\text{DD}}$ and 12.5 V to V $_{\text{PP}}$.
- (6) Select program inhibit mode.
- (7) Write data in 1-ms write mode.
- (8) Select program inhibit mode.
- (9) Select verify mode. If the write operation is found successful, proceed to step (10). If the operation is found unsuccessful, repeat steps (7) to (9).
- (10) Perform additional write for X (number of repetitions of steps (7) to (9)) \times 1 ms.
- (11) Select program inhibit mode.
- (12) Increment the program memory address by one on reception of four pulses on the CLK pin.
- (13) Repeat steps (7) to (12) until the last address is reached.
- (14) Select program memory address clear mode.
- (15) Apply 5 V to the V DD and VPP pins.
- (16) Turn power off.

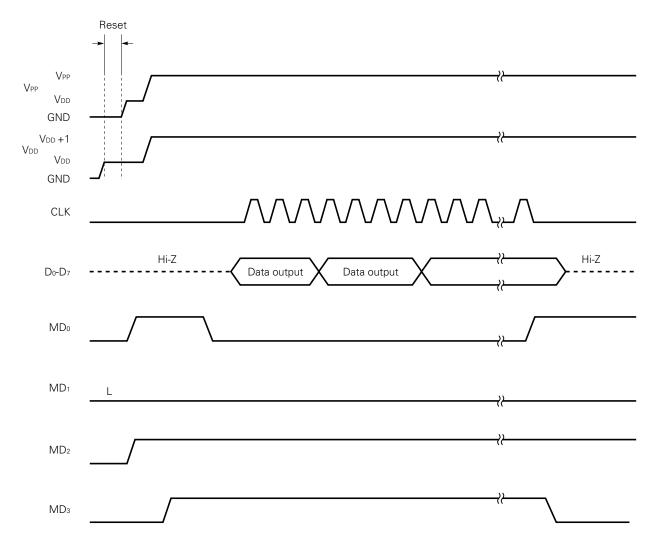
A timing chart for program memory writing steps (2) to (12) is shown below.



3.3 READING PROGRAM MEMORY

- (1) Pull low the levels of all unused pins to GND by means of resistors (the X our pin is left open). Bring CLK to low level.
- (2) Apply 5 V to V DD and bring VPP to low level.
- (3) Wait 10 μ s. Then apply 5 V to V PP.
- (4) Set the mode selection pins to program memory address clear mode.
- (5) Apply 6 V to V $_{\text{DD}}$ and 12.5 V to V $_{\text{PP}}$.
- (6) Select program inhibit mode.
- (7) Select verify mode. Data is output sequentially one address at a time for every four input clock pulses on the CLK.
- (8) Select program inhibit mode.
- (9) Select program memory address clear mode.
- (10) Apply 5 V to the V DD and VPP pins.
- (11) Turn power off.

A timing chart for program memory reading steps (2) to (9) is shown below.



★ 4. ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS (T_A = 25 $^{\circ}$ C)

Parameter	Symbol		Conditions	Rated value	Unit
Power supply voltage	Vdd			-0.3 to +7.0	V
Input voltage	Vı	P0A, P0B, RESET	P0C, P0E1 ^{Note} , INT,	-0.3 to V _{DD} + 0.3	V
		P0D, P0E₀		-0.3 to +10.0	V
Output voltage	Vo	P0A, P0B, F	POC, POE1 ^{Note}	-0.3 to VDD + 0.3	V
		P0D, P0E₀		-0.3 to +10.0	V
High-level output current	I output current Iон Each of P0A, P0B, and P0C		A, P0B, and P0C	-5	mA
		Total of all output pins		-20	mA
Low-level output current	lol	Each of P0	A, P0B, and P0C	5	mA
		Each of PO	D and P0E	30	mA
		Total of P0/ pins	A, P0B, and P0C output	20	mA
		Total of P0	D and P0E output pins	60	mA
		Total of all	output pins	80	mA
Operating ambient temperature	TA			-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C
Allowable dissipation	Pd	T _A = 85 °C	Plastic shrink DIP	155	mW
			Plastic SOP	95	mW

- **Note** The P0E₁ N-ch open-drain input/output pin cannot be used as an intermediate-withstand-voltage port pin.
- Caution Absolute maximum ratings are rated values beyond which some physical damages may be caused to the product; if any of the parameters in the table above exceeds its rated value even for a moment, the quality of the product may deteriorate. Be sure to use the product within the rated values.

RECOMMENDED POWER VOLTAGE RANGE (TA = -40 to +85 °C)

Parameter	Conditions	Min.	Тур.	Max.	Unit
opu Noto	Oscillator frequency: $fx = 400 \text{ kHz to 4 MHz}$	2.7		5.5	V
CPU ^{Note}	Oscillator frequency: fx = 400 kHz to 8 MHz	4.5		5.5	V
Power-on/power-down reset circuit	Rising time of the power voltage (V _{DD} = 0 \rightarrow 2.7 V): 4096tcy or less (fx = 400 kHz to 4 MHz)	4.5		5.5	V

Note Excluding the power-on/power-down reset circuit

Remark tcy = 16/fx (fx: frequency of the system clock oscillator)

DC CHARACTERISTICS (V_{DD} = 2.7 to 5.5 V, T_A = -40 to +85 $^{\circ}$ C)

Parameter	Symbol		Cond	itions	Min.	Тур.	Max.	Unit	
High-level input	VIH1	P0A, P	0B, P0C, P0D,	, P0E	0.7V _{DD}		VDD	V	
voltage	VIH2	RESET	, SCK, SI, INT	-	0.8VDD		VDD	V	
Low-level input	VIL1	P0A, P	0B, P0C		0		0.3VDD	V	
voltage	VIL2	P0D, P	0E, RESET, S	CK, SI, INT	0		0.2VDD	V	
High-level output				V _{DD} = 4.5 to 5.5 V Іон = -1.0 mA	V _{DD} - 0.3			V	
voltage	Vон	P0A, P0	0B, P0C -	V _{DD} = 2.7 to 4.5 V Іон = -0.5 mA	V _{DD} - 0.3			V	
		P0A, P0	0B, P0C,	V _{DD} = 4.5 to 5.5 V I _{OL} = 1.0 mA			0.3	V	
Low-level output	Vol1		POD, PO		V _{DD} = 2.7 to 4.5 V I _{OL} = 0.5 mA			0.3	V
voltage				V _{DD} = 4.5 to 5.5 V I _{OL} = 15 mA			1.0	V	
	Vol2	P0D, P0	JE –	V _{DD} = 2.7 to 4.5 V I _{OL} = 15 mA			2.0	V	
High-level input leakage current	Іцн	· ·	P0A, P0B, P0C, P0D, P0E VIN = VDD				3	μA	
Low-level input leakage current	Lu	P0A, P0 VIN = 0	0B, P0C, P0D, V	, P0E			-3	μΑ	
High-level output leakage current	Ігон	Р0А, Р0 Vout =	0B, P0C, P0D, Vdd	, P0E			3	μΑ	
Low-level output leakage current	ILOL	Р0А, Р0 Vout =	0B, P0C, P0D, 0 V	, P0E			-3	μΑ	
			fx = 8.0 MHz	z, Vdd = 5 V \pm 10 %		5.0	8.0	mA	
			fx = 4.0 MHz	z, Vdd = 5 V \pm 10 %		3.0	5.0	mA	
	IDD1	Oper- ating	fx = 2.0 MHz	z, VDD = $3 V \pm 10 \%$		1.0	2.5	mA	
		mode	fy _ 455 kHz	$V_{DD} = 5 V \pm 10 \%$		2.0	4.5	mA	
			fx = 455 kHz	VDD = 3 V ±10 %		0.7	2.2	mA	
Power supply			fx = 8.0 MHz	z, Vdd = 5 V \pm 10 %		3.5	5.0	mA	
current ^{Note}			fx = 4.0 MHz	z, Vdd = 5 V ± 10 %		2.5	3.5	mA	
	IDD2	HALT mode	fx = 2.0 MHz	z, Vdd = 3 V ±10 %		0.8	2.0	mA	
		mode	4 455 111	$V_{DD} = 5 V \pm 10 \%$		1.8	3.5	mA	
			fx = 455 kHz	V _{DD} = 3 V ±10 %		0.6	1.9	mA	
	IDD3	STOP	$V_{DD} = 5 V \pm$	10 %		3.0	10	μA	
		mode	$V_{DD} = 3 V \pm$	10 %		2.0	10	μA	

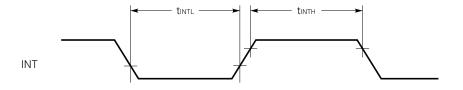
Note This current excludes the current which flows through the comparator.

AC CHARACTERISTICS (VDD = 2.7 to 5.5 V, TA = -40 to +85 $^\circ\text{C})$

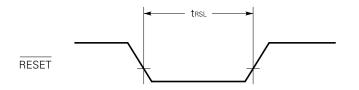
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
CPU clock cycle time	tcy	V _{DD} = 4.5 to 5.5 V	1.9		41	μs
(instruction execution time)			3.9		41	μs
INT high/low level	tinтн,	V _{DD} = 4.5 to 5.5 V	10			μs
width (external interrupt input)	t INTL		50			μs
RESET low level width	trsl	V _{DD} = 4.5 to 5.5 V	10			μs
			50			μs

Remark tcy = 16/fx (fx: frequency of system clock oscillator)

Interrupt Input Timing



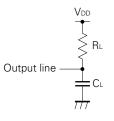
RESET Input Timing

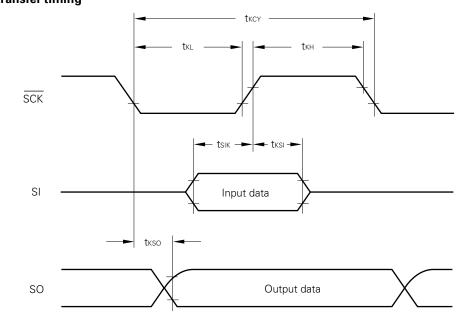


SERIAL TRANSFER OPERATION (VDD = 2.7 to 5.5 V, TA = -40 to +85 °C)

Parameter	Symbol		Conditions	i	Min.	Тур.	Max.	Unit
SCK cycle time	tксу	out	V _{DD} = 4.5 to 5.5 V		2.0			μs
		lup			10			μs
		Output	$R_{L} = 1 \ k\Omega, \ C_{L} = 100 \ pF$	V _{DD} = 4.5 to 5.5 V	2.0			μs
		Out			16			μs
SCK high/low level	tкн,	ut	V _{DD} = 4.5 to 5.5 V		1.0			μs
width	tĸ∟	lnp			5.0			μs
		put	$R_L = 1 \ k\Omega, \ C_L = 100 \ pF$	V _{DD} = 4.5 to 5.5 V	tксу/2-0.6			μs
		Output			tксу/2-1.2			μs
SI setup time (with respect to \overline{SCK})	tsıк				100			ns
SI hold time (with respect to \overline{SCK})	tksi				100			ns
Delay from SCK↓ to	tкso	R∟⊧	= 1 kΩ, CL = 100 pF	V _{DD} = 4.5 to 5.5 V			0.8	μs
SO							1.4	μs

Remark R_L and C_L are a resistive load and a capacitive load for the output line.





Serial transfer timing

POWER-ON/POWER-DOWN RESET CIRCI	JIT CHARACTERISTICS (T _A = -40 to $+85$ °C)
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Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Power voltage rise time when power-on reset is valid	tpor	$V_{DD} = 0 \rightarrow 2.7 \text{ V}$ Rising must start at 0 V. fx = 400 kHz to 4 MHz			4096tcy	μs
Voltage for power- down reset circuit	Vpdr	When PDRESEN = 1		3.5	4.5	V

Remark tcy = 16/fx (fx: frequency of the system clock oscillator)

COMPARATOR CHARACTERISTICS (VDD = 2.7 to 5.5 V, $T_A = -40$ to +85 °C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Comparator input voltage range	VAIN	Cino - Cin3, V _{ref}	0		Vdd	V
ResolutionNote 1		V _{DD} = 4.5 to 5.5 V		10	50	mV
nesolution					100	mV
Response time		Note 2			6t cy	μs

Notes 1. Also applied to the condition that the internal reference voltage is used.

2. Time required for storing the comparison result in CMPRSLT after execution of the comparator start instruction (execution time not included). (12 μ s, when fx = 8 MHz)

Remark tcy = 16/fx (fx: frequency of the system clock oscillator)

SYSTEM CLOCK OSCILLATOR CHARACTERISTICS (VDD = 2.7 to 5.5 V, TA = -40 to +85 $^{\circ}$ C)

Resonator	Parameter	Conditions	Min.	Тур.	Max.	Unit
Ceramic resonator	Oscillation		0.39		4.08	MHz
	frequency (f _X)	V _{DD} = 4.5 to 5.5 V	0.39		8.16	MHz

DC PROGRAMMING CHARACTERISTICS (V_{DD} = 6.0 ± 0.25 V, V_PP = 12.5 ± 0.5 V, T_A = 25 $^{\circ}C$)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage high	VIH1	Except CLK	0.7Vdd		Vdd	V
pat tonagog.	VIH2	CLK	VDD - 0.5		Vdd	V
Input voltage low	VIL1	Except CLK	0		0.3Vdd	V
pat renage ten	VIL2	CLK	0		0.4	V
Input leakage current	lu	VIN = VIL or VIH			10	μA
Output voltage high	Vон	Іон = −1 mA	VDD - 1.0			V
Output voltage low	Vol	lol = 1.6 mA			0.4	V
VDD power supply current	ldd				30	mA
V _{PP} power supply current	Ірр	MD0 = VIL, MD1 = VIH			30	mA

Cautions 1. VPP must be under +13.5 V including overshoot.

2. VDD must be applied before VPP on and must be off after VPP off.

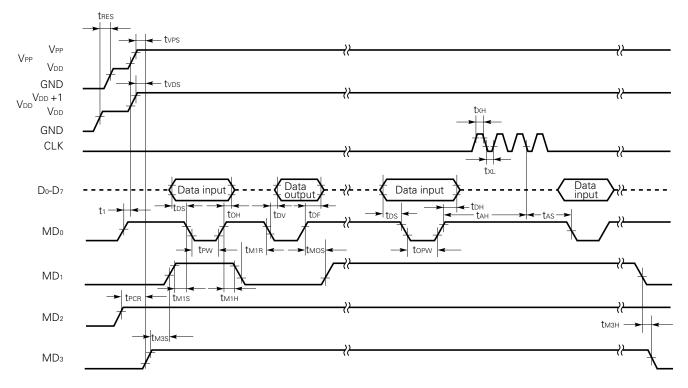
AC PROGRAMMING CHARACTERISTICS (V_DD = 6.0 ± 0.25 V, VPP = 12.5 ± 0.5 V, TA = 25 $^\circ\text{C}$)

Parameter	Symbol	Note 1	Conditions	Min.	Тур.	Max.	Unit
Address setup time $^{Note\ 2}$ to MD0 \downarrow	tas	tas		2			μs
MD1 setup time to MD0 \downarrow	t _{M1S}	toes		2			μs
Data setup time to MD0 \downarrow	tos	tos		2			μs
Address hold time ^{Note 2} to MD0↑	tан	tан		2			μs
Data hold time to MD0↑	tрн	tон		2			μs
Delay from MD0↑ to data output float	tdf	tdf		0		130	ns
V _{PP} setup time to MD3↑	tvps	tvps		2			μs
V _{DD} setup time to MD3↑	tvds	tvcs		2			μs
Initial program pulse width	tpw	tew		0.95	1.0	1.05	ms
Additional program pulse width	topw	topw		0.95		21.0	ms
MD0 setup time to MD1↑	tмos	tces		2			μs
Delay from MD0 \downarrow to data output	tdv	tov	MD0 = MD1 = VIL			1	μs
MD1 hold time to MD0↑	tм1н	tоен		2			μs
MD1 recovery time to MD0 \downarrow	tm₁r	tor	tм1н + tм1к≧ 50 μs	2			μs
Program counter reset time	t PCR	_		10			μs
CLK input high, low level range	tхн, tх∟	_		0.125			μs
CLK input frequency	fx	_				2	MHz
Initial mode set time	tı	-		2			μs
MD3 setup time to MD1↑	tмзs	-		2			μs
MD3 hold time to MD1 \downarrow	tмзн	-		2			μs
MD3 setup time to MD0↓	tмзsr	_	Read program memory	2			μs
Delay from address ^{Note 2} to data output	t dad	tacc	Read program memory			2	μs
Hold time from address ^{Note 2} to data output	thad	tон	Read program memory	0		130	ns
MD3 hold time to MD0↑	tмзнк	_	Read program memory	2			μs
Delay from MD3↓ to data output float	tdfr	_	Read program memory			2	μs
Reset setup time	tres			10			μs

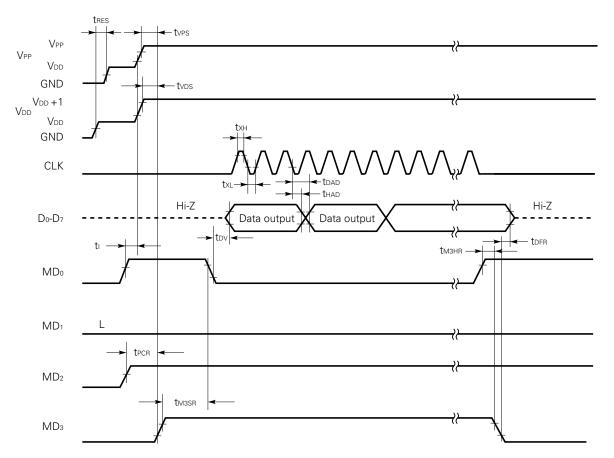
Notes1. Corresponding symbol for μ PD27C256A (used for maintenance)

2. The internal address is incremented by one at the falling edge of the third clock (CLK) input.

Write program memory timing



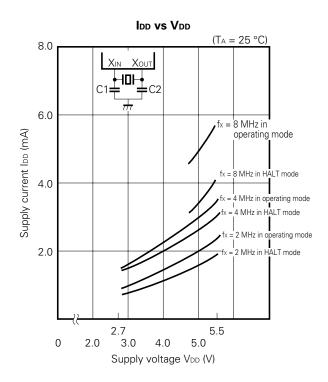
Read program memory timing



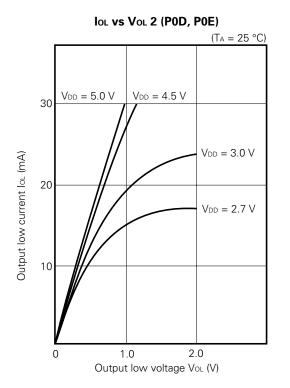
Remark The dashed line indicates high-impedance.

5. CHARACTERISTIC CURVES (FOR REFERENCE)

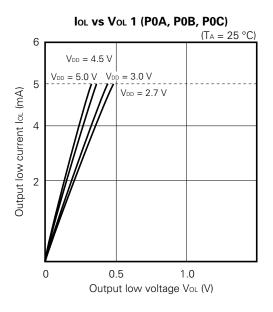
NEC

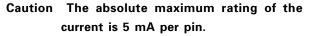


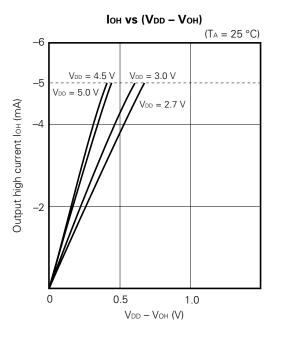
Caution The absolute maximum rating of the current is 5 mA per pin.



Caution The absolute maximum rating of the current is 30 mA per pin. The input voltage or output voltage of the P0E 1 pin must not be higher than 1⁄20 + 0.3 V.



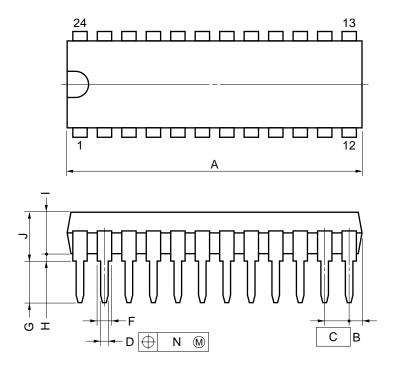


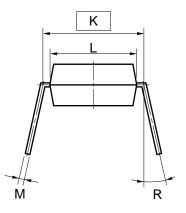


Caution The absolute maximum rating of the current is -5 mA per pin.

6. PACKAGE DRAWINGS

24 PIN PLASTIC SHRINK DIP (300 mil)



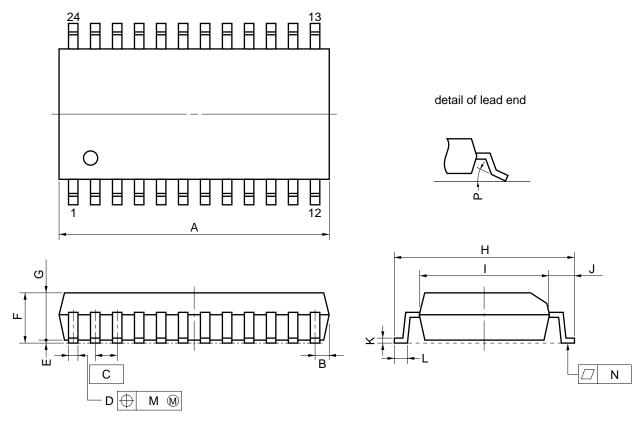


NOTE

- 1) Each lead centerline is located within 0.17 mm (0.007 inch) of its true position (T.P.) at maximum material condition.
- 2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
Α	23.12 MAX.	0.911 MAX.
В	1.78 MAX.	0.070 MAX.
С	1.778 (T.P.)	0.070 (T.P.)
D	0.50±0.10	$0.020^{+0.004}_{-0.005}$
F	0.85 MIN.	0.033 MIN.
G	3.2±0.3	0.126±0.012
Н	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.08 MAX.	0.200 MAX.
К	7.62 (T.P.)	0.300 (T.P.)
L	6.5	0.256
М	$0.25^{+0.10}_{-0.05}$	$0.010^{+0.004}_{-0.003}$
Ν	0.17	0.007
R	0~15°	0~15°
		S24C-70-300B-1

24 PIN PLASTIC SOP (375 mil)



NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES	
Α	15.54 MAX.	0.612 MAX.	
В	0.78 MAX.	0.031 MAX.	
С	1.27 (T.P.)	0.050 (T.P.)	
D	$0.40^{+0.10}_{-0.05}$	$0.016^{+0.004}_{-0.003}$	
Е	0.1±0.1	0.004±0.004	
F	2.9 MAX.	0.115 MAX.	
G	2.50	0.098	
Н	10.3±0.3	$0.406^{+0.012}_{-0.013}$	
I	7.2	0.283	
J	1.6	0.063	
К	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.002}$	
L	0.8±0.2	$0.031\substack{+0.009\\-0.008}$	
М	0.12	0.005	
Ν	0.15	0.006	
Р	3° ^{+7°} -3°	$3^{\circ}^{+7^{\circ}}_{-3^{\circ}}$	
		24GM-50-375B-3	

P24GM-50-375B-3

7. RECOMMENDED SOLDERING CONDITIONS

The conditions listed below shall be met when soldering the μ PD17P133.

For details of the recommended soldering conditions, refer to our document *SMD Surface Mount Technology Manual* (IEI-1207).

Please consult with our sales offices in case any other soldering process is used, or in case soldering is done under different conditions.

Table 7-1 Soldering Conditions for Surface-Mount Devices

μ PD17P133GT: 24-pin plastic SOP (375 mil)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	 Peak package's surface temperature: 235 °C Reflow time: 30 seconds or less (at 210 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. </cautions> (2) Do not use water for flux cleaning before a second reflow soldering. 	IR35-207-2
VPS	 Peak package's surface temperature: 215 °C Reflow time: 40 seconds or less (at 200 °C or more) Maximum allowable number of reflow processes: 2 Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125 °C afterward.) <cautions> (1) Do not start reflow-soldering the device if its temperature is higher than the room temperature because of a previous reflow soldering. (2) Do not use water for flux cleaning before a second reflow soldering. </cautions> 	VP15-207-2
Wave soldering	Temperature in the soldering vessel: 260 °C or less Soldering time: 10 seconds or less Number of soldering process: 1 Preheating temperature: 120 °C max. (measured on the package surface) Exposure limit: 7 daysNote (20 hours of pre-baking is required at 125 °C afterward.)	WS60-207-1
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each side of device)	

Note Exposure limit before soldering after dry-pack package is opened.

Storage conditions: Temperature of 25 °C and maximum relative humidity at 65 % or less

Caution Do not apply more than a single process at once, except for "Partial heating method."

Table 7-2 Soldering Conditions for Through Hole Mount Devices

μ PD17P133CS: 24-pin plastic shrink DIP (300 mil)

Soldering process	Soldering conditions
Wave soldering (only for terminals)	Solder temperature: 260 °C or less Flow time: 10 seconds or less
Partial heating method	Terminal temperature: 300 °C or less Flow time: 3 seconds or less (for each terminal)

Caution In wave soldering, apply solder only to the terminals. Care must be taken that jet solder does not come in contact with the main body of the package.

APPENDIX A $\ \mu \text{PD17120}$ SUB-SERIES PRODUCTS LIST

Product name	μPD17120	μPD17132	μPD17P132	μPD17121	μPD17133	μPD17P133
ROM capacity	Masked ROM		One-time PROM	Masked ROM		One-time PROM
	1.5K bytes (768 × 16 bits)	, ,		1.5K bytes (768 × 16 bits)	2K bytes (1024 × 16 bits)	
RAM capacity	64×4 bits	111×4 bits		64×4 bits	111 × 4 bits	
Number of input/ output port pins	19 (Input/output pins: 18, Sensor input pins (INT pins): 1)					
External interrupt	1 (with sensor	1 (with sensor input)				
Analog input	None Comparators (4 channels)			None	Comparators (4 channels)	
Timer	1 channel					
Serial interface	1 channel					
Stack	Five address stacks and one interrupt stack					
Power-on/power-down reset circuit	Built-in (Can be used in an application circuit where V_{DD} is 5 V ± 10 %)			Built-in (Can be used in an application circuit where V_DD is 5 V ± 10 % and fx = 400 kHz to 4 MHz		
System clock	RC oscillation			Ceramic oscillation		
Instruction execution time	8 μs at fcc = 2 MHz			2 μ s at fx = 8 MHz		
Standby function	HALT, STOP					
Supply voltage	 V_{DD} = 2.7 to 5.5 V V_{DD} = 4.5 to 5.5 V (when the power-on/power-down reset function is used) 					
Package	 24-pin plastic shrink DIP (300 mil) 24-pin plastic SOP (375 mil) 					
One-time PROM product	μPD17P132		_	μPD17P133		_

Remark The comparator can be used as a 4-bit A/D converter by software.

APPENDIX B DEVELOPMENT TOOLS

The following support tools are available for developing programs for the μ PD17P133.

Hardware

Name	Description
In-circuit emulator [IE-17K IE-17K-ETNote 1 EMU-17KNote 2	The IE-17K, IE-17K-ET, and EMU-17K are in-circuit emulators applicable to the 17K series. The IE-17K and IE-17K-ET are connected to the PC-9800 series (host machine) or IBM PC/AT TM through the RS-232-C interface. The EMU-17K is inserted into the extension slot of the PC-9800 series (host machine). Use the system evaluation board (SE board) corresponding to each product together with one of these in-circuit emulators. SIMPLEHOST TM , a man machine interface, implements an advanced debug environment. The EMU-17K also enables user to check the contents of the data memory in real time.
SE board (SE-17120)	The SE-17120 is an SE board for the μ PD17120 sub-series. It is used solely for evaluating the system. It is also used for debugging in combination with the in-circuit emulator.
Emulation probe (EP-17120CS)	The EP-17120CS is an emulation probe for the 17K series 24-pin shrink DIP (300 mil). Use this emulation probe to connect the SE board to target system.
PROM programmer AF-9703Note 3 AF-9704Note 3 AF-9705Note 3 AF-9706Note 3	The AF-9703, AF-9704, AF-9705, and AF-9706 are PROM programmers for the μ PD17P133. Use one of these PROM programmers with the program adapter, AF-9808M, to write a program into the μ PD17P133.
Program adapter (AF-9808M ^{Note 3})	The AF-9808M is a socket unit for the μ PD17P133CS or μ PD17P133GT. It is used with the AF-9703, AF-9704, AF-9705, or AF-9706.

Notes 1. Low-end model, operating on an external power supply

- 2. The EMU-17K is a product of IC Co., Ltd. Contact IC Co., Ltd. (Tokyo, 03-3447-3793) for details.
- **3**. The AF-9703, AF-9704, AF-9705, AF-9706, and AF-9808M are products of Ando Electric Co., Ltd. Contact Ando Electric Co., Ltd. (Tokyo, 03-3733-1151) for details.

Software

Name	Description	Host machine	05	6	Distribution media	Part number
17K series assembler			MS-DOS [™]		5.25-inch, 2HD	μS5A10AS17K
(AS17K)	17K) In developing µPD17P133 programs, AS17K is used in combination with a device file (AS17133).				3.5-inch, 2HD	μS5A13AS17K
		IBM PC/AT	PC DOS™		5.25-inch, 2HC	μ S7B10AS17K
					3.5-inch, 2HC	μ S7B13AS17K
Device file (AS17133)	AS17133 is a device file for the μ PD17133 and μ PD17P133	PC-9800 series	MS-DOS		5.25-inch, 2HD	μ S5A10AS17120 Note
	It is used together with the assembler (AS17K), which is applicable to the 17K series.				3.5-inch, 2HD	μS5A13AS17120 Note
		IBM PC/AT	PC DOS		5.25-inch, 2HC	μS7B10AS17120 Note
					3.5-inch, 2HC	μS7B13AS17120 Note
Support software (SIMPLEHOST)	SIMPLEHOST, running on the	PC-9800 series	MS-DOS	Windows	5.25-inch, 2HD	μS5A10ΙΕ17Κ
Windows TM , provides man- machine-interface in devel- oping programs by using a personal computer and the in-circuit emulator.	machine-interface in devel-				3.5-inch, 2HD	μS5A13ΙΕ17Κ
	personal computer and the	IBM PC/AT	PC DOS		5.25-inch, 2HC	μS7B10IE17K
						3.5-inch, 2HC

Note μ SXXXAS17120 indicates the AS17120, AS17121, AS17132, and AS17133.

Remark The following table lists the versions of the operating systems described in the above table.

OS	Versions
MS-DOS	Ver. 3.30 to Ver. 5.00ANote
PC DOS	Ver. 3.1 to Ver. 5.0Note
Windows	Ver. 3.0 to Ver. 3.1

Note MS-DOS versions 5.00 and 5.00A and PC DOS Ver. 5.0 are provided with a task swap function. This function, however, cannot be used in these software packages.

*

Cautions on CMOS Devices

Countermeasures against static electricity for all MOSs

Caution When handling MOS devices, take care so that they are not electrostatically charged. Strong static electricity may cause dielectric breakdown in gates. When transporting or storing MOS devices, use conductive trays, magazine cases, shock absorbers, or metal cases that NEC uses for packaging and shipping. Be sure to ground MOS devices during assembling. Do not allow MOS devices to stand on plastic plates or do not touch pins. Also handle boards on which MOS devices are mounted in the same way.

\$ CMOS-specific handling of unused input pins

Caution Hold CMOS devices at a fixed input level.

Unlike bipolar or NMOS devices, if a CMOS device is operated with no input, an intermediate-level input may be caused by noise. This allows current to flow in the CMOS device, resulting in a malfunction. Use a pull-up or pull-down resistor to hold a fixed input level. Since unused pins may function as output pins at unexpected times, each unused pin should be separately connected to the VDD or GND pin through a resistor. If handling of unused pins is documented, follow the instructions in the document.

% $\,$ Statuses of all MOS devices at initialization $\,$

Caution The initial status of a MOS device is unpredictable when power is turned on.

Since characteristics of a MOS device are determined by the amount of ions implanted in molecules, the initial status cannot be determined in the manufacture process. NEC has no responsibility for the output statuses of pins, input and output settings, and the contents of registers at power on. However, NEC assures operation after reset and items for mode setting if they are defined.

When you turn on a device having a reset function, be sure to reset the device first.

NEC

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NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

- Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices in "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact NEC Sales Representative in advance.

Anti-radioactive design is not implemented in this product.

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